

# **ISC Silicon NPN RF Transistor**

#### **DESCRIPTION**

- · Low Base Time Constant;
  - $r_{bb'} \cdot cC = 4 \text{ ps TYP}.$
- High Gain Bandwidth Product

fT= 2 GHz TYP. @ I<sub>E</sub>= -5mA, V<sub>CE</sub>= 10V

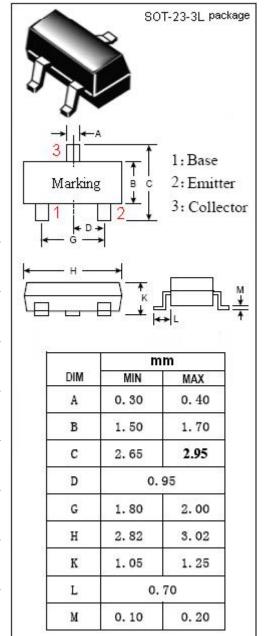
- · Low Feedback Capacitance;
  - $C_{re} = 0.48 pF TYP.$
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

 Designed for use as UHF oscillator and mixer in a tuner of a TV receiver.

# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL           | PARAMETER                               | VALUE   | UNIT |
|------------------|---|---------|------|
| V <sub>CBO</sub> | Collector-Base Voltage                  | 30      | ٧    |
| $V_{\text{CEO}}$ | Collector-Emitter Voltage               | 15      | V    |
| V <sub>EBO</sub> | Emitter-Base Voltage                    | 3       | V    |
| Ic               | Collector Current-Continuous            | 50      | mA   |
| Pc               | Collector Power Dissipation<br>@Tc=25°C | 0.15    | W    |
| TJ               | Junction Temperature                    | 125     | °C   |
| T <sub>stg</sub> | Storage Temperature Range               | -65~125 | °C   |





## **ISC Silicon NPN RF Transistor**

2SC3545

### **ELECTRICAL CHARACTERISTICS**

 $T_{\text{C}}$ =25°C unless otherwise specified

| SYMBOL                             | PARAMETER                            | CONDITIONS   | MIN | TYP. | MAX | UNIT |
|------------------------------------|--------------------------------------|--|-----|------|-----|------|
| V <sub>CE(sat)</sub>               | Collector-Emitter Saturation Voltage | I <sub>C</sub> = 10mA ; I <sub>B</sub> = 1mA             |     |      | 0.5 | V    |
| І <sub>СВО</sub>                   | Collector Cutoff Current             | V <sub>CB</sub> = 12V; I <sub>E</sub> = 0                |     |      | 0.1 | μА   |
| h <sub>FE</sub>                    | DC Current Gain                      | I <sub>C</sub> = 5mA ; V <sub>CE</sub> = 10V             | 50  |      | 250 |      |
| f⊤                                 | Current-Gain—Bandwidth Product       | I <sub>E</sub> = -5mA ; V <sub>CE</sub> = 10V            | 1.3 | 2.0  |     | GHz  |
| Cre                                | Feedback Capacitance                 | I <sub>E</sub> = 0 ; V <sub>CB</sub> = 10V;f= 1.0MHz     |     | 0.48 | 1.0 | pF   |
| r <sub>bb</sub> , • C <sub>C</sub> | Base Time Constant                   | V <sub>CE</sub> = 10V,I <sub>E</sub> = -5mA,f = 31.9 MHz |     | 4    | 10  | ps   |

#### h<sub>FE</sub> Classifications

| Class           | M/P    | L/Q    | K/R     |
|-----------------|--------|--------|---------|
| Marking         | T42    | T43    | T44     |
| h <sub>FE</sub> | 50-100 | 70-140 | 120-250 |

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